

N-channel 100 V 4.8 mΩ standard level MOSFET in D2PAK 12 April 2013 Product data sheet

### 1. General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. Part of Nexperia's "NextPower Live" portfolio, the PSMN4R8-100BSE complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn on, whilst offering a low  $R_{DS(on)}$  characteristic to keep temperatures down and efficiency up in continued use. Ideal for telecommunication systems based on a 48 V backplane / supply rail.

#### 2. Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low R<sub>DS(on)</sub> for low conduction losses

### 3. Applications

**T**. I. I. A

- Electronic fuse
- Hot swap
- Load switch
- Soft start

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#### 4. Quick reference data

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Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>DM</sub>	peak drain current	pulsed; $T_{mb}$ = 25 °C; $t_p \le 10 \ \mu$ s; Fig. 4	-	-	707	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	405	W
Static charac	teristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	-	4.1	4.8	mΩ
Dynamic cha	racteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V;	-	59	83	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15	-	196	278	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche Ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 ^{\circ}\text{C};  \text{I}_{\text{D}} = 120 \text{ A}; \\ V_{sup} \leq 100 \text{ V};  \text{R}_{GS} = 50  \Omega; \text{ unclamped}; \\ \hline \text{Fig. 3}$		-	-	542	mJ

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

[1] It is not possible to make connection to pin 2

### 6. Ordering information

### Table 3 Ordering information

Type number	Package				
	Name	Description	Version		
PSMN4R8-100BSE	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

### 7. Marking

Table 4. Marking codes			
Type number	Marking code		
PSMN4R8-100BSE	PSMN4R8-100BSE		

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	M	lin	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-		100	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-		100	V
V <sub>GS</sub>	gate-source voltage		-2	20	20	V
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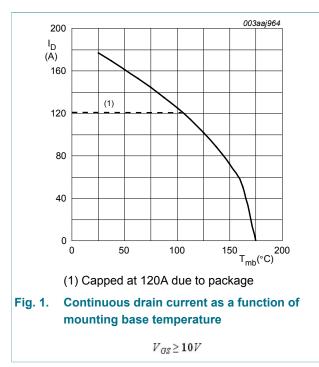
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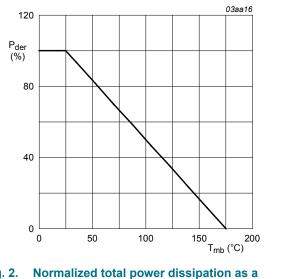
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Symbol	Parameter	Conditions		Min	Мах	Unit
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	120	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 4		-	707	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	405	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	707	А
Avalanche F	Ruggedness		-			
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω; unclamped; Fig. 3		-	542	mJ

[1] Continuous current limited by package.





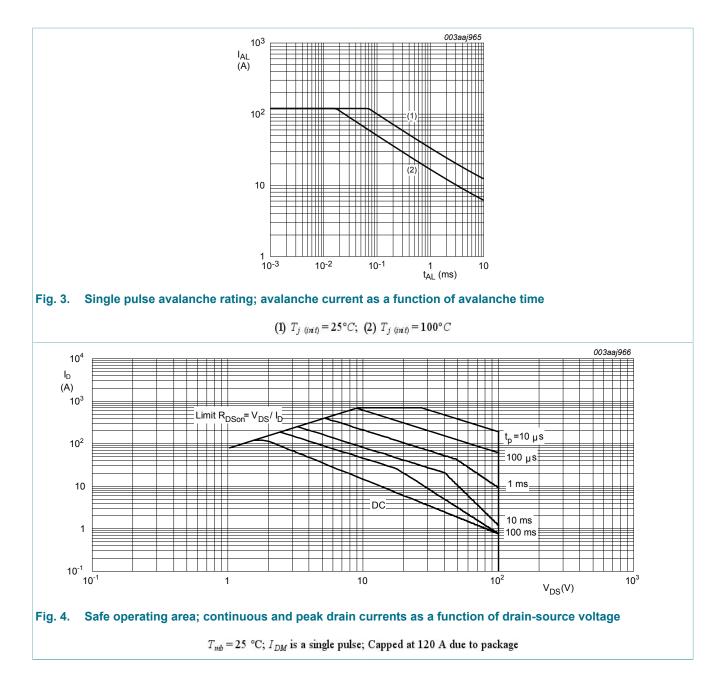


 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$ 

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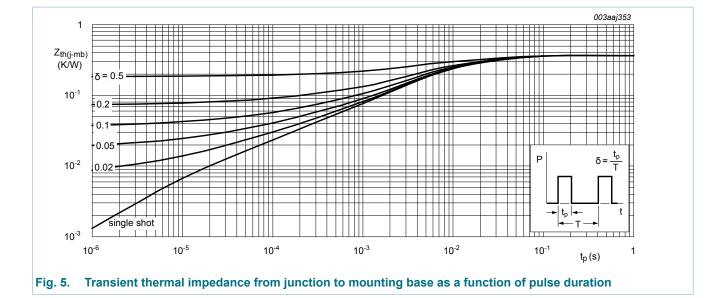
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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.3	0.37	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

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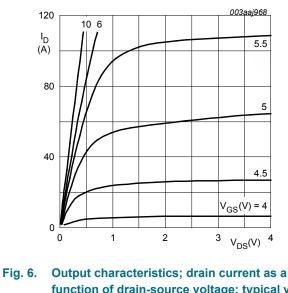
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2	3	4	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 11	1	-	-	V
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 11	-	-	4.6	V	
I <sub>DSS</sub> drain leakage current	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.16	10	μA
	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA	
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	-	4.1	4.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13; Fig. 12	-	-	8.7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	-	13	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.43	0.85	1.7	Ω

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	196	278	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	166.9	234	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V;	-	40	56	nC
Q <sub>GD</sub>	gate-drain charge	<u>Fig. 14; Fig. 15</u>	-	59	83	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 14; Fig. 15</u>	-	4.3	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	10665	14400	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	674	910	pF
C <sub>rss</sub>	reverse transfer capacitance		-	459	643	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V;	-	41	61.5	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	65	97.5	ns
t <sub>d(off)</sub>	turn-off delay time		-	127	190.5	ns
t <sub>f</sub>	fall time		-	69	103.5	ns
Source-dra	in diode	· · · ·	I			
V <sub>SD</sub>	source-drain voltage	$I_{\rm S}$ = 25 A; $V_{\rm GS}$ = 0 V; $T_{\rm j}$ = 25 °C; Fig. 17	-	0.79	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	72	94	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V	-	227	296	nC





 $T_j = 25^{\circ}C$ 

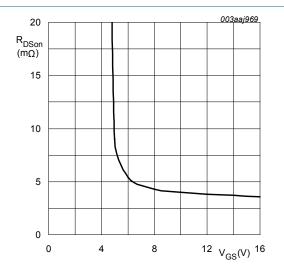


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

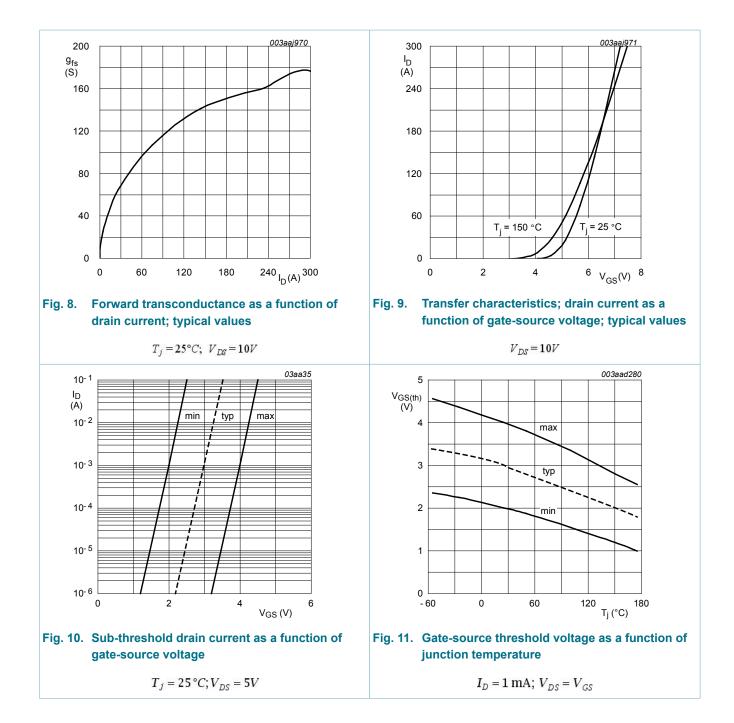
 $T_j = 25^{\circ}C; \ I_D = 25A$ 

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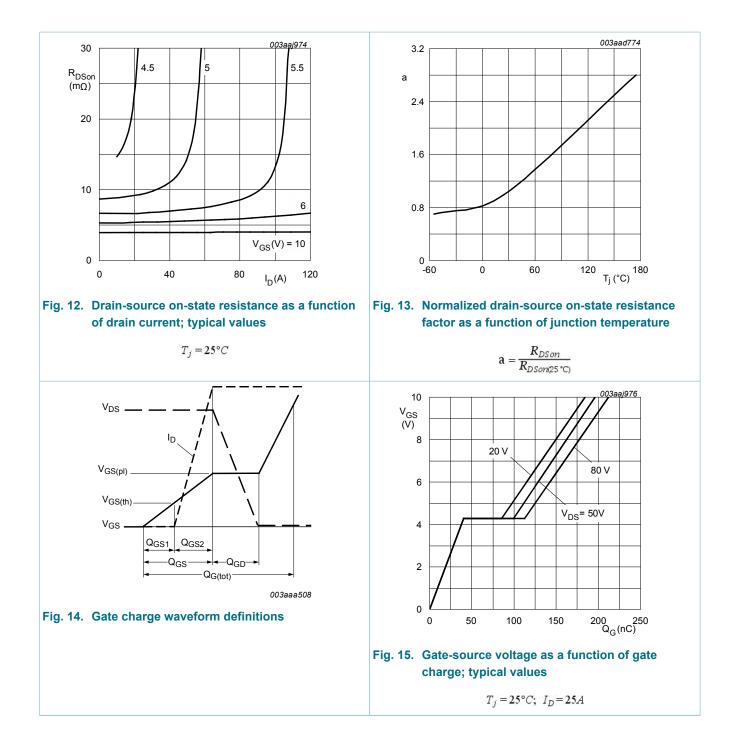
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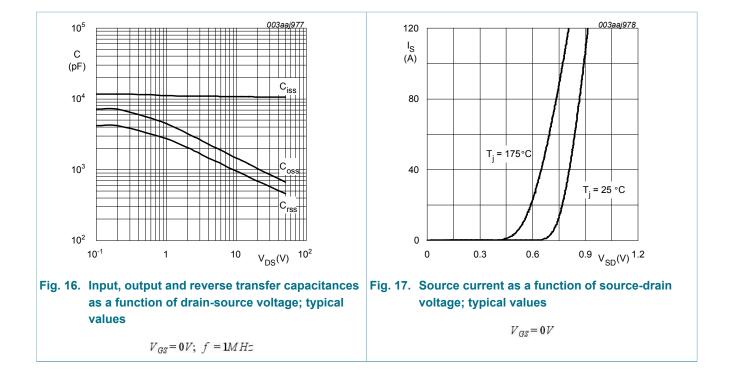
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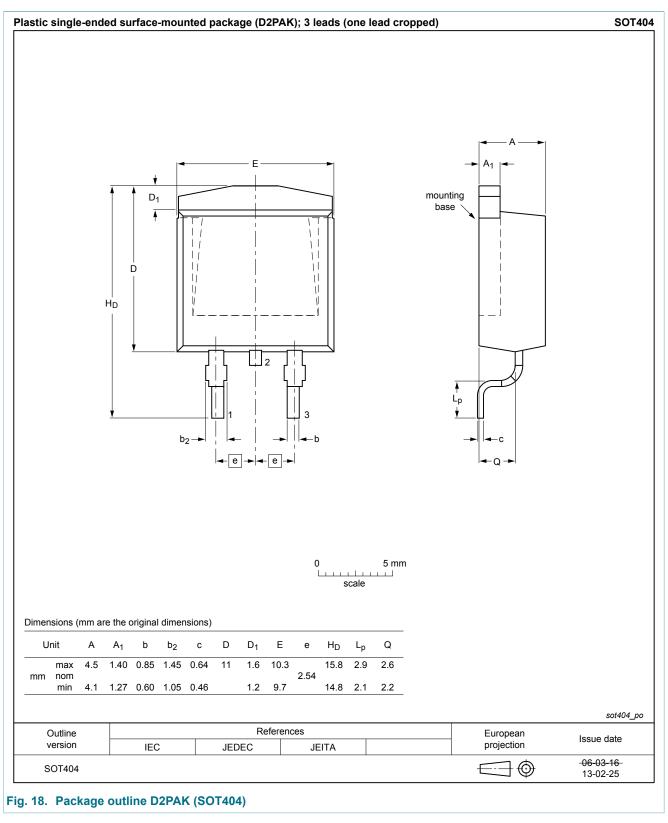
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### 11. Package outline



#### N-channel 100 V 4.8 m $\Omega$ standard level MOSFET in D2PAK

#### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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